



PCN# : P5C9AA
Issue Date : Apr. 04, 2016

DESIGN/PROCESS CHANGE NOTIFICATION

This is to inform you that a change is being made to the products listed below.

Unless otherwise indicated in the details of this notification, the identified change will have no impact on product quality, reliability, electrical, visual or mechanical performance and affected products will remain fully compliant to all published specifications. Products incorporating this change may be shipped interchangeably with existing unchanged products.

This change is planned to take effect in 90 calendar days from the date of this notification. Please work with your local Fairchild Sales Representative to manage your inventory of unchanged product if your evaluation of this change will require more than 90 calendar days.

Please contact your local Customer Quality Engineer within 30 days of receipt of this notification if you require any additional data or samples.

Implementation of change:

Expected First Shipment Date for Changed Product :Jul. 03, 2016

Expected First Date Code of Changed Product :1627

Description of Change (From) :
8 inch wafer fabrication at TowerJazz Israel

Description of Change (To) :
8-inch wafer fabrication at Fairchild in Bucheon, South Korea
and 8-inch wafer fabrication at TowerJazz Israel

Reason for Change:
Fairchild Semiconductor is increasing wafer fabrication capacity by qualifying 8-inch wafer fabrication line at Fairchild Semiconductor Bucheon Korea. Quality and reliability remain at the highest standards already demonstrated within Fairchild's existing products. The reliability qualification results used to qualify the 8-inch wafer fabrication line are summarized below. Design, die size and layout of the affected products will remain unchanged. There are no changes in the datasheet or electrical performance.

Affected Product(s):

2N7000	2N7000_D26Z	2N7000_D74Z
2N7000_D75Z	2N7002	2N7002_D87Z
2N7002_G	9G85_BSS138	9G85_MMBF170
9GA85_2N7000	BS170	BS170_D26Z
BS170_D27Z	BS170_D74Z	BS170_D75Z
BS270	BS270_D74Z	BSS138
BSS138_D87Z	BSS138_G	MMBF170
MMBF170_G	MTD3055V	MTD3055VL
MTP3055VL	NDB5060L	NDB6060L
NDC7001C	NDC7002N	NDP6060
NDP6060L	NDP7060	NDS7002A
NDS9945	NDT014	NDT014L
NDT3055	NDT3055L	

Qualification Plan	Device	Package	Process	No. of Lots
Q20150527	NDP7060	TO-220	3.8N	3

Test Description:	Condition:	Standard :	Duration:	Results:
High Temperature Gate Bias	175°C, Vgs = 20V	JESD22-A108	1000 hrs	0/231
High Temperature Reverse Bias	175°C, Vr = 48V	JESD22-A108	1000 hrs	0/231
High Temperature Storage Life	175°C	JESD22-A103	1000 hrs	0/231
Highly Accelerated Stress Test	130°C, 85%RH, Vr = 48V	JESD22-A110	96 hrs	0/231
Power Cycle	Delta 100CC, 3.5 Min cycle	MIL-STD-750-1036	8572 cycles	0/231
Temperature Cycle	-65°C, 150°C	JESD22-A104	1000 cycles	0/231